

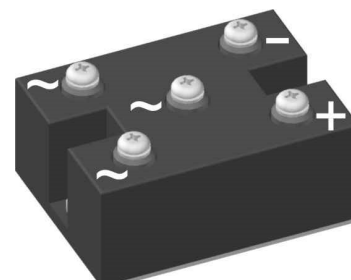
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1200 \text{ V}$
$I_{DAV} = 120 \text{ A}$
$I_{FSM} = 1500 \text{ A}$

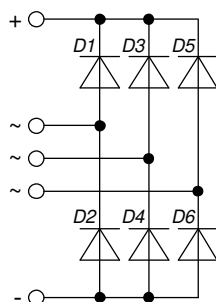
3~ Rectifier Bridge

Part number

VUO105-12NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-C

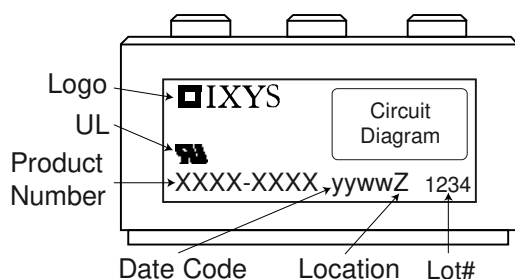
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 40\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.09	V
		$I_F = 120\text{ A}$				1.38	V
		$I_F = 40\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.00	V
		$I_F = 120\text{ A}$				1.36	V
I_{DAV}	bridge output current	$T_C = 105^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ $d = \frac{1}{3}$			120	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.78	V
r_F	slope resistance					4.8	m Ω
R_{thJC}	thermal resistance junction to case					0.8	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				155	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1.50	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.62	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.28	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.38	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			11.3	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			10.9	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			8.13	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7.87	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			58		pF

Package PWS-C				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				150	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					250		g
M_D	mounting torque			4.25		5.75	Nm
M_T	terminal torque			4.25		5.75	Nm
$d_{Spp/Apb}$	creepage distance on surface striking distance through air	terminal to terminal		26.0			mm
$d_{Spb/Apb}$		terminal to backside		14.0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V
		t = 1 minute		2500			V

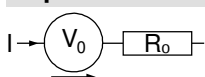


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO105-12NO7	VUO105-12NO7	Box	10	456713

Equivalent Circuits for Simulation

* on die level

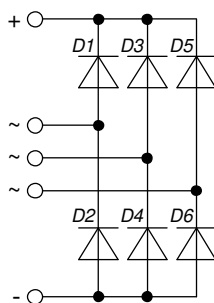
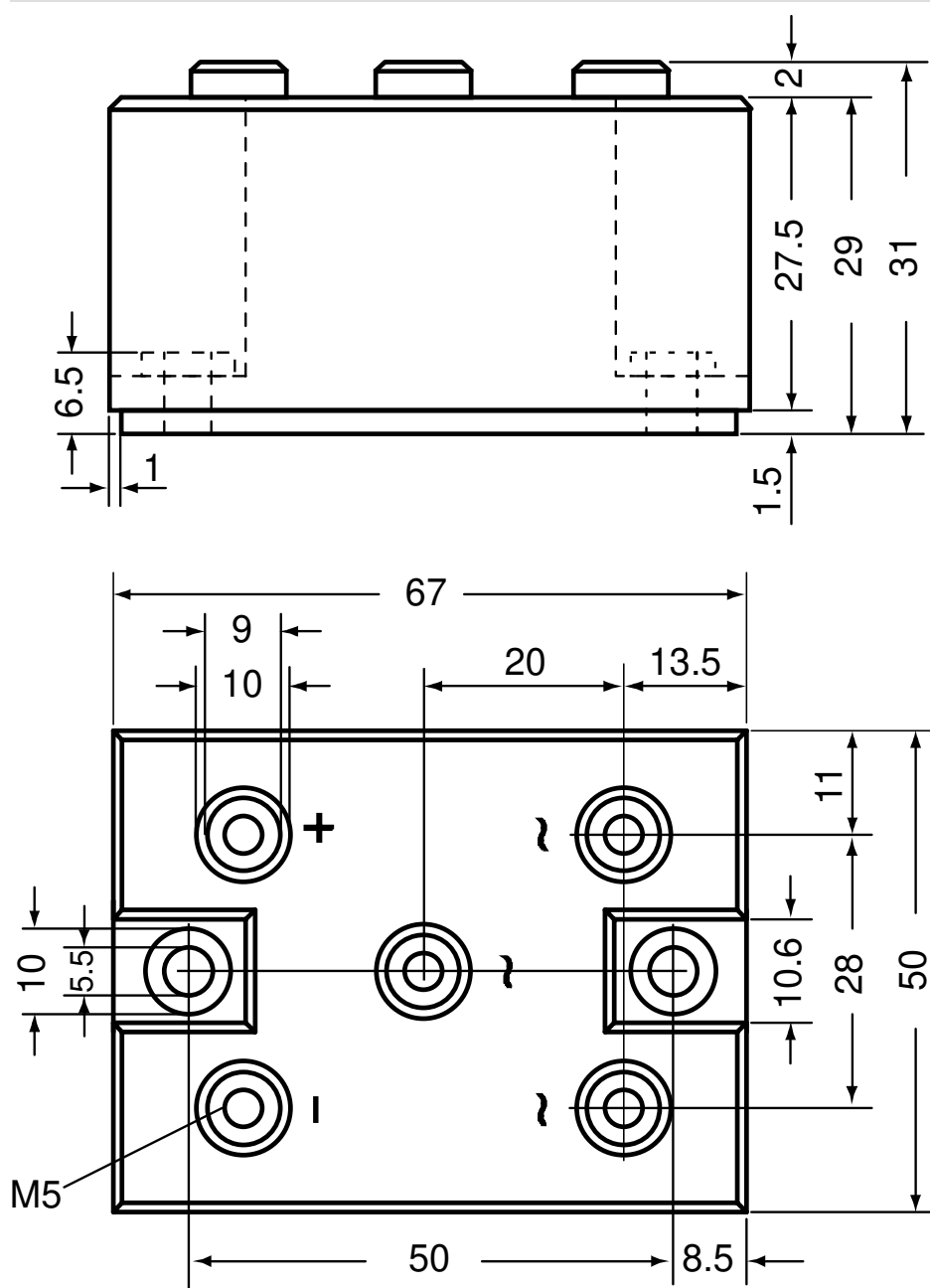
$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

$V_{0\max}$	threshold voltage	0.78	V
$R_{0\max}$	slope resistance *	3.6	mΩ

Outlines PWS-C



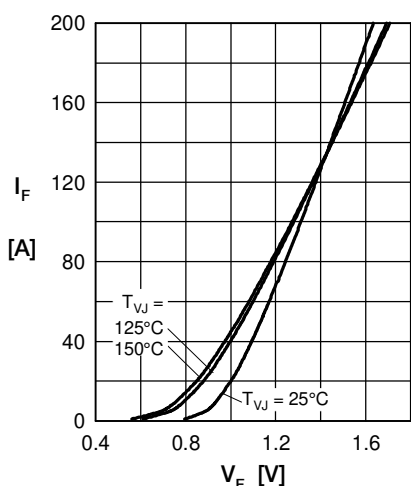
Rectifier


Fig. 1 Forward current versus voltage drop per diode

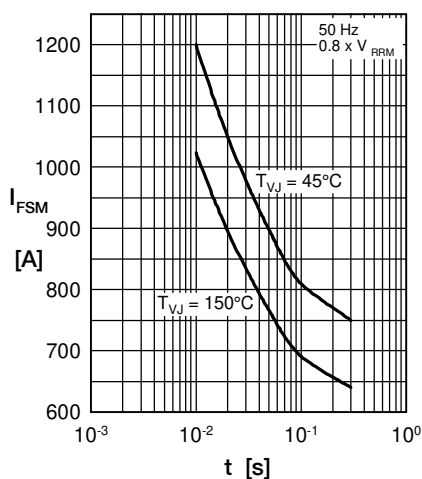


Fig. 2 Surge overload current vs. time per diode

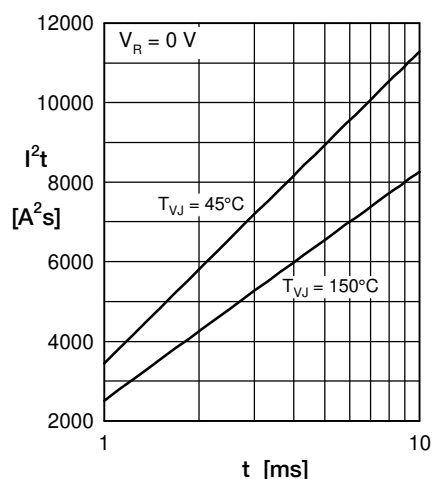
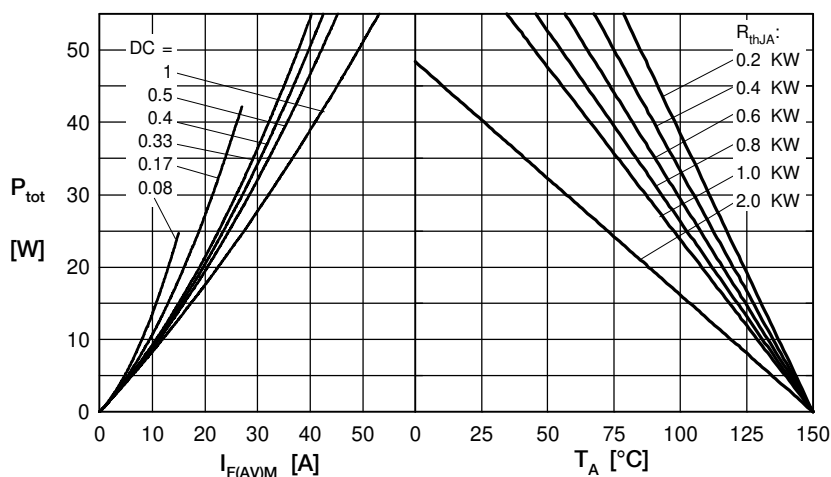

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

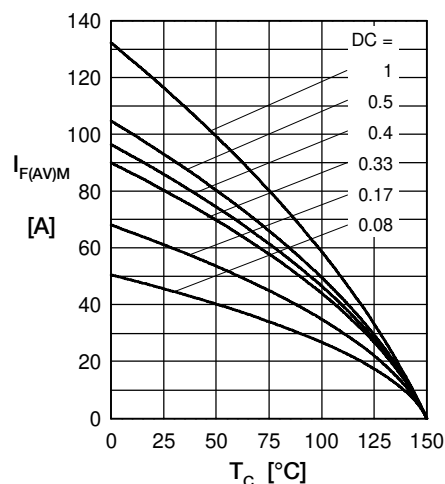


Fig. 5 Max. forward current vs. case temperature per diode

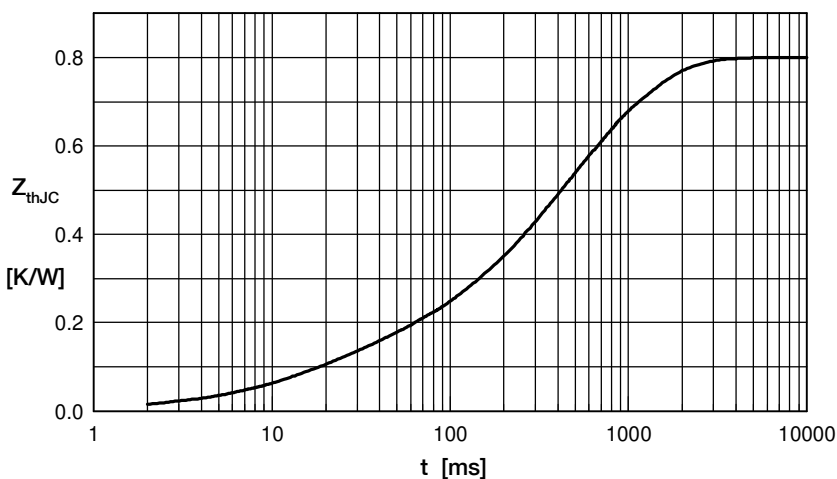


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.100	0.020
2	0.014	0.010
3	0.192	0.225
4	0.281	0.800
5	0.213	0.580